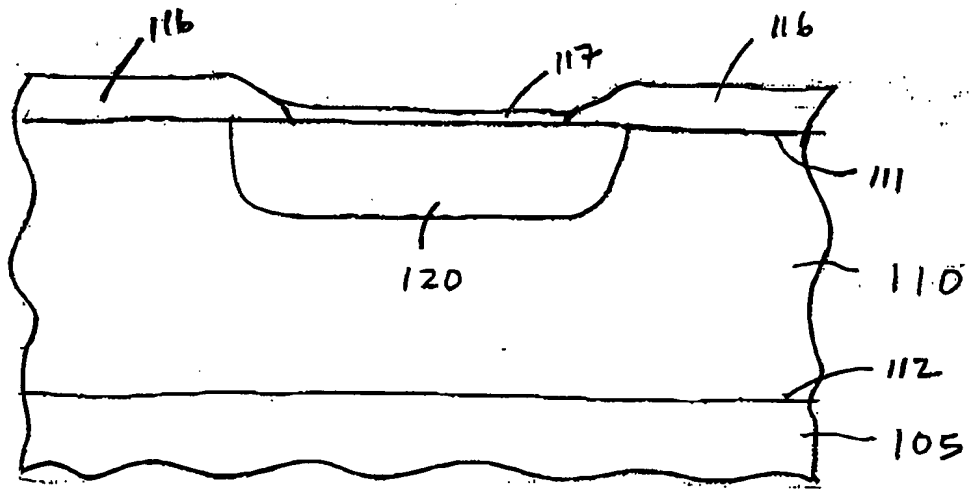
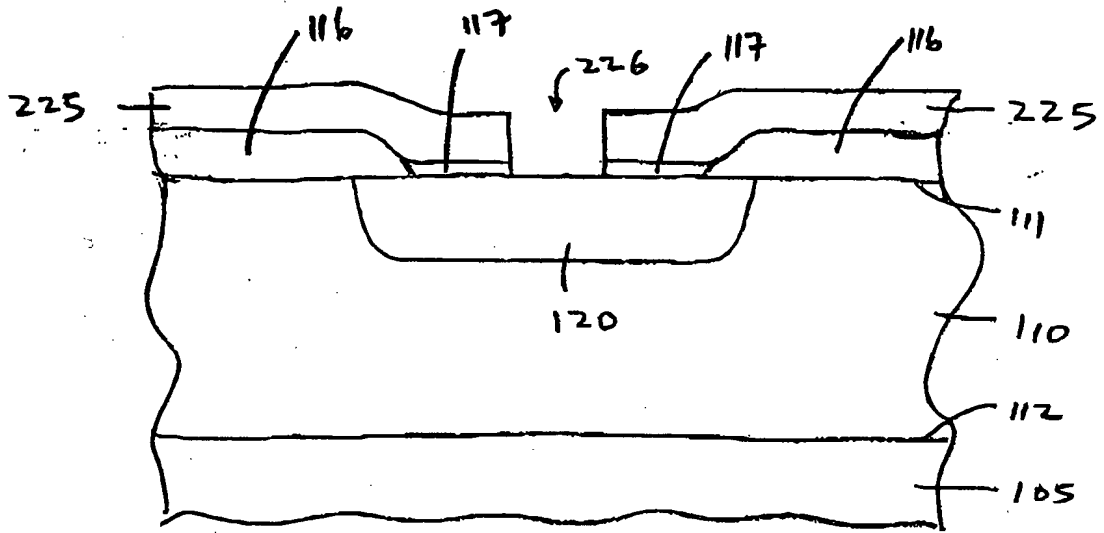


09802726-031201



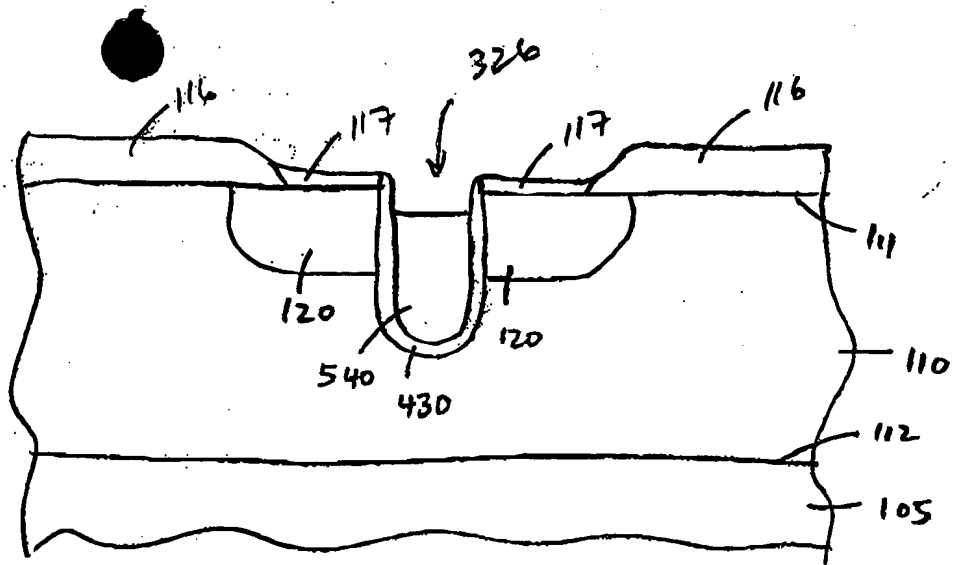
100
FIG. 1



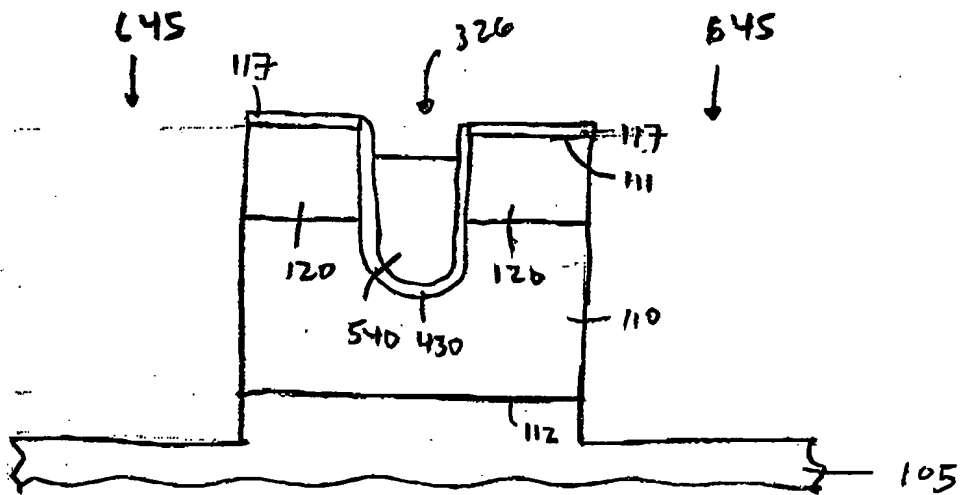
100
FIG. 2

A cross-sectional view of a semiconductor device. A central trench, labeled 430, is formed in a substrate 105. The trench is lined with a material 435. The trench is filled with a material 320. The trench is surrounded by a material 111. The trench is further surrounded by a material 110. The trench is further surrounded by a material 112. The trench is further surrounded by a material 105. The trench is further surrounded by a material 116. The trench is further surrounded by a material 117. The trench is further surrounded by a material 120.

100
FIG. 4



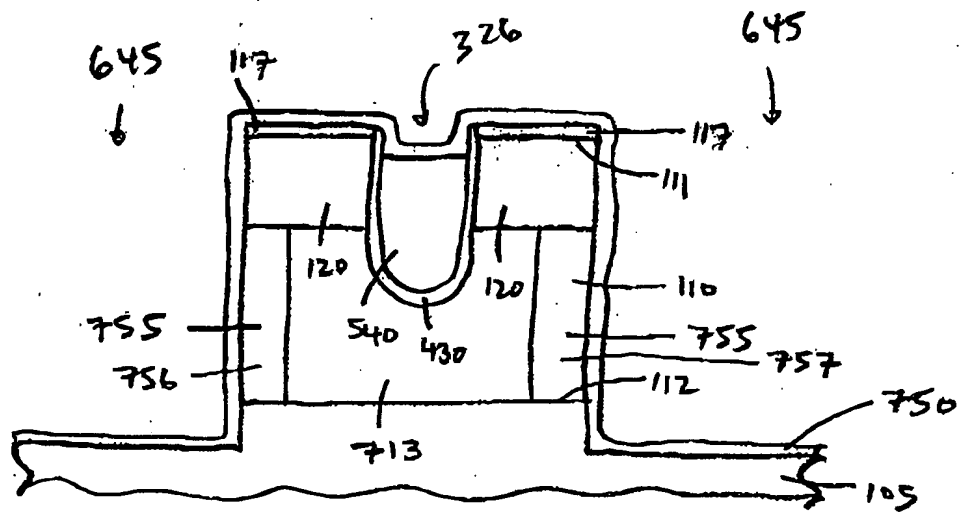
100
FIG. 5



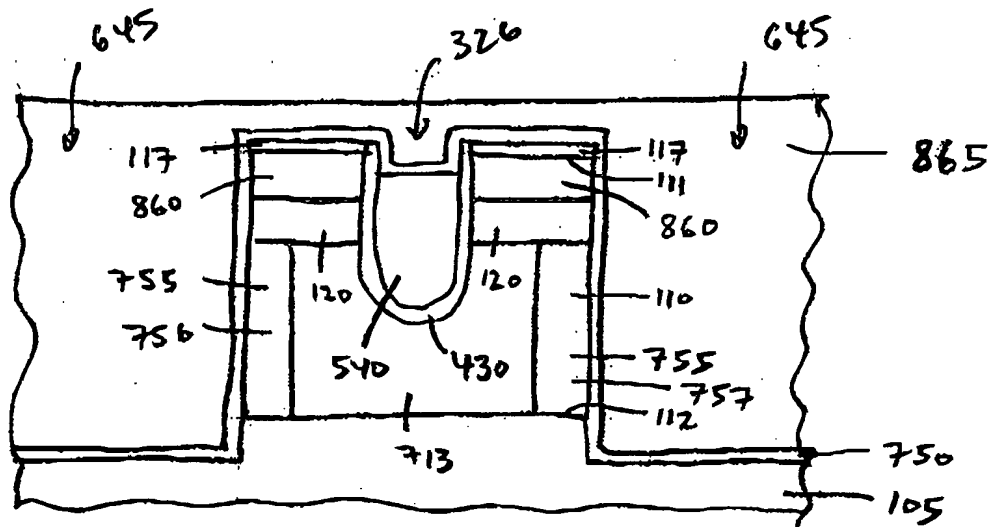
100
FIG. 6

00002726-021201

00002725:031201

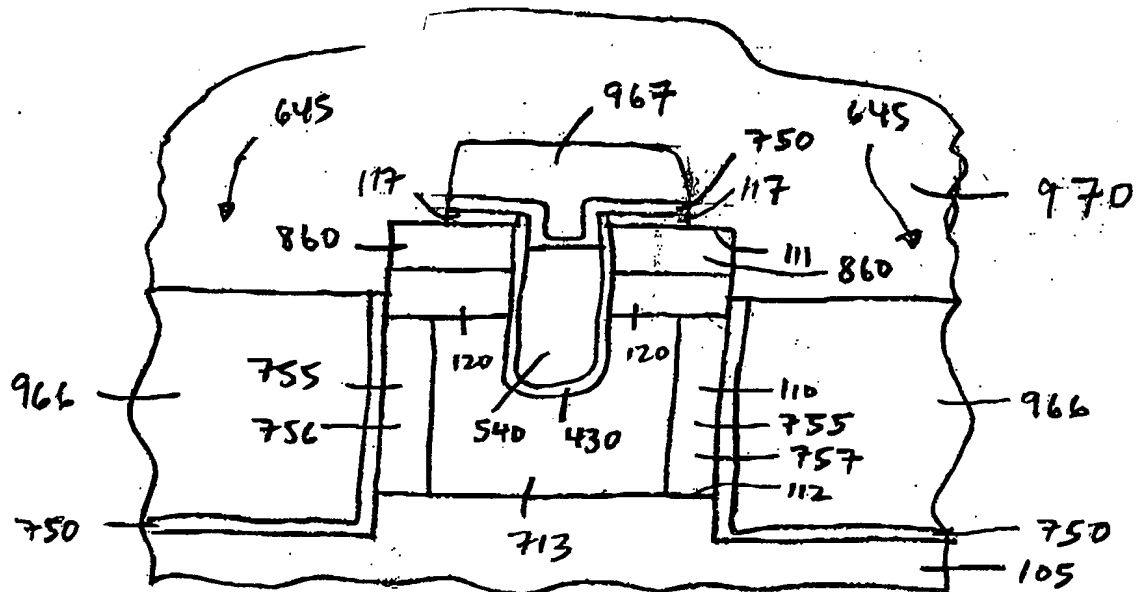


100
FIG. 7



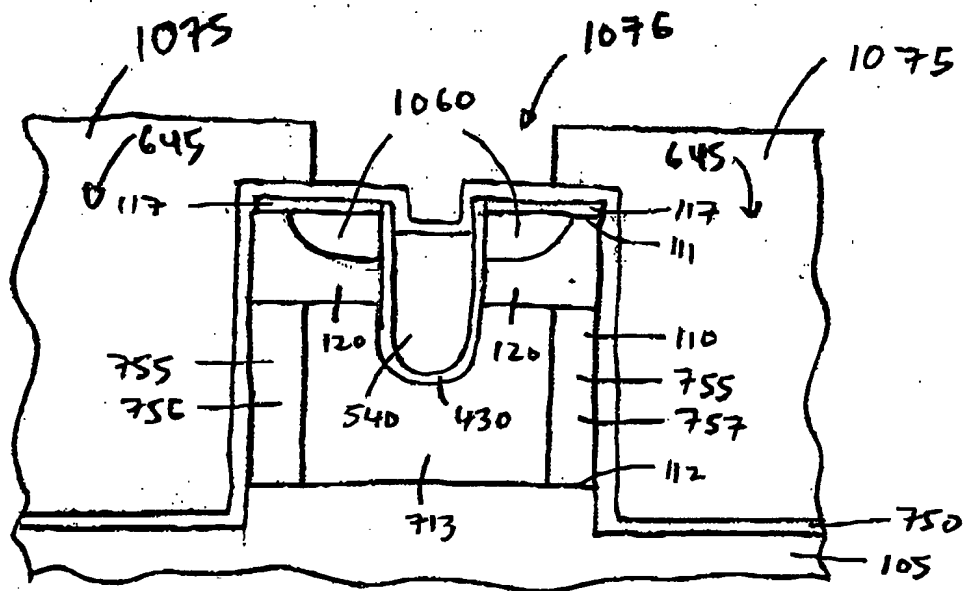
100
FIG. 8

00002726-031201

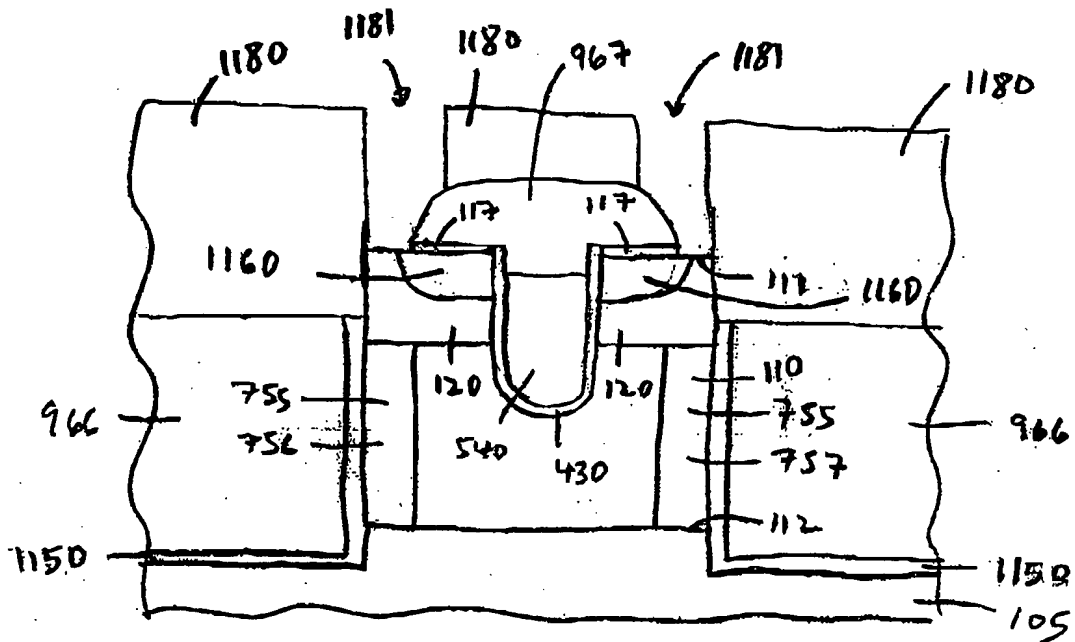


100
FIG. 9

09802726-034201

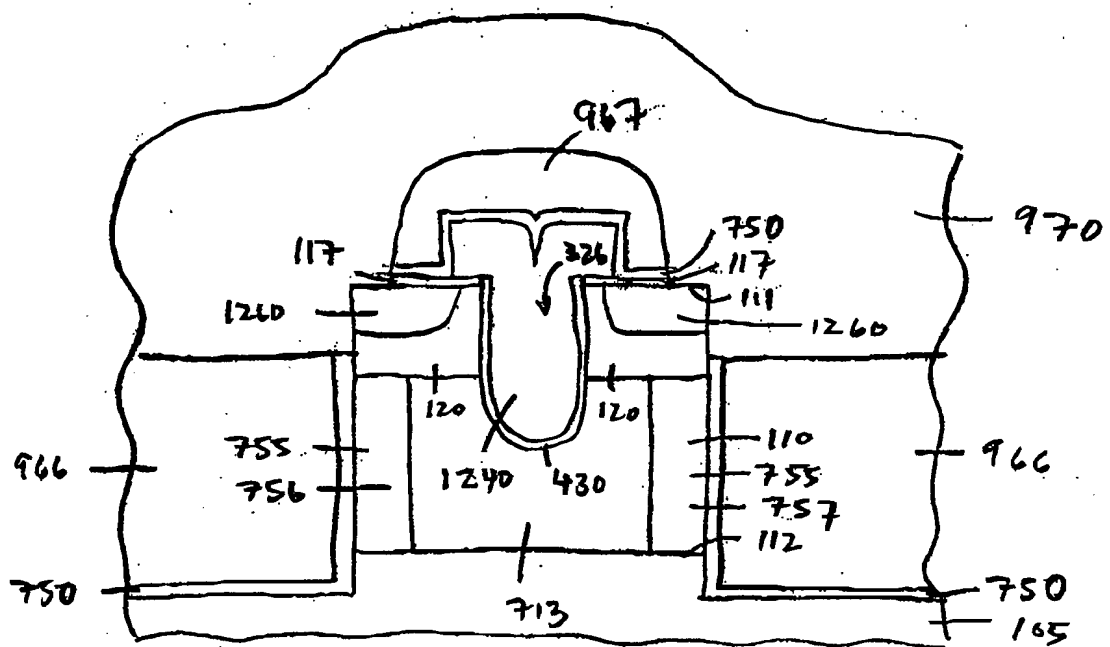


1000
FIG. 10



1100
FIG. 11

000002726-031201



1200
FIG. 12

FIG. 13

1300

